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2. (Amended) The semiconductor device according to claim 1, wherein the crystalline film, when subjected to X-ray diffraction, has a spectrum having a first peak between 36 degrees and 38 degrees and a second peak between 42 degrees and 44 degrees.
3. (Amended) The semiconductor device of claim 2, wherein a half-width of the first peak is 3.2 degrees or less.
4. (Amended) The semiconductor device of claim 2, wherein a half-width of the second peak is 2.6 degrees or less.
5. (Amended) A semiconductor device comprising:
 - an insulator film formed on a substrate;
 - a wiring layer of copper formed on the insulator film; and
 - a crystalline film for preventing copper diffusion from the wiring layer to the insulator film, the crystalline film formed of a material comprising tungsten, carbon, and nitrogen, the crystalline film arranged between the insulator film and the wiring layer.

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14. (New) A semiconductor device comprising:
 - an insulator film formed on a substrate;
 - a crystalline film formed on the insulator; and
 - a wiring layer of copper formed on the crystalline film,wherein the crystalline film prevents copper diffusion from the wiring layer to the insulator film.
15. (New) The semiconductor device according to claim 14, wherein the crystalline film comprises WC_xN_y .

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16. (New) The semiconductor device according to claim 14, wherein the crystalline film, when subjected to X-ray diffraction, has a spectrum having a first peak between 36 degrees and 38 degrees and a second peak between 42 degrees and 44 degrees.
17. (New) The semiconductor device according to claim 16, wherein a half-width of the first peak is 3.2 degrees or less.
18. (New) The semiconductor device according to claim 16, wherein a half-width of the second peak is 2.6 degrees or less.

REMARKS

In the Office Action dated January 15, 2002, the Examiner acknowledges the claim for foreign priority under 35 U.S.C. § 119(a)-(d) and 365(c) and the receipt of certified copies of the priority documents. However, the Examiner fails to acknowledge, in item 15 of the Office Action Summary, a claim for domestic priority under 35 U.S.C. § 120. Thus, Applicant respectfully requests the Examiner to acknowledge the claim for domestic priority under 35 U.S.C. § 120 in the next communication.

In the outstanding Office Action, the Examiner: objected to drawings; objected to specification; rejected claims 1 and 5 under 35 U.S.C. § 102(b) as being anticipated by Ueno (JP 10-209073); rejected claims 1 and 5 under 35 U.S.C. § 102(e) as being anticipated by Vitkavage et al. (U.S. Patent No. 5,858,873); rejected claims 2-4 under 35 U.S.C. § 103(a) as being unpatentable over Ueno (JP 10-209073); and rejected claims 2-4 under 35 U.S.C. § 103(a) as being unpatentable over in view of Vitkavage et al. (U.S. Patent No. 5,858,873).

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